



**International
Semiconductor, Inc.**

**IDB050
thru
1DB1000**

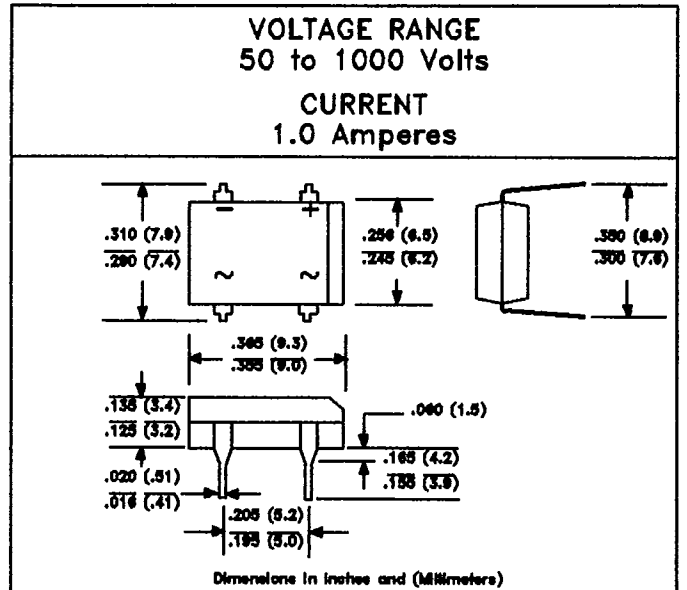
DUAL-IN-LINE GLASS PASSIVATED SINGLE PHASE BRIDGE

FEATURES:

- Plastic material used carries Underwriters Laboratory recognition 94 V-0
- Low Leakage
- Surge overload rating - 30 amperes peak
- Ideal for printed circuit board applications
- Exceeds environmental standards of MIL-STD 19500

MECHANICAL DATA:

- CASE:** Reliable low cost construction utilizing transfer molding techniques
- TERMINALS:** Leads Solderable per MIL-STD-202, Method 208
- POLARITY:** Polarity symbols molded on body
- MOUNTING POSITION:** Any
- WEIGHT:** 0.04 OUNCE (1.0 GRAM)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified
 Single phase, half wave, 60 Hz, resistive or inductive load
 For capacitive load, derate current by 20%

	1DB050	1DB100	1DB200	1DB400	1DB600	1DB800	1DB1000	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Ta = 40 C	1.0							A
Maximum Forward Surge Current 8.3 ms single half sine wave superimposed on rated load	30.0							A
I ² t Rating For Fusing (t < 8.35 ms)	5.0							A ² t
Maximum Forward Voltage Drop per Bridge Element at 1.0 Amp	1.1							V
Maximum DC Reverse Current at Rated Tj=25C DC Blocking Voltage per element Tj=125C	5.0 0.5							ua ma
Operating Temperature Range	-55 to +125							C
Storage Temperature Range	-55 to +150							C

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DUAL-IN-LINE GLASS PASSIVATED SINGLE PHASE BRIDGE 1DB050 thru 1DB1000 RATING AND CHARACTERISTIC CURVES

FIG. 1 - MAXIMUM NON-REPETITIVE SURGE CURRENT

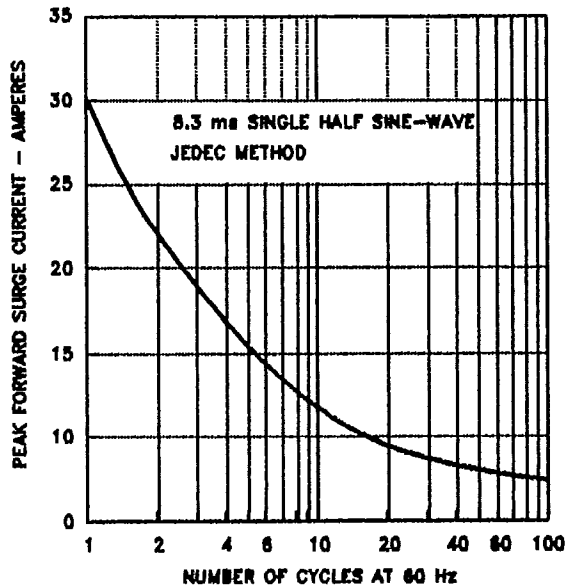


FIG. 2 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

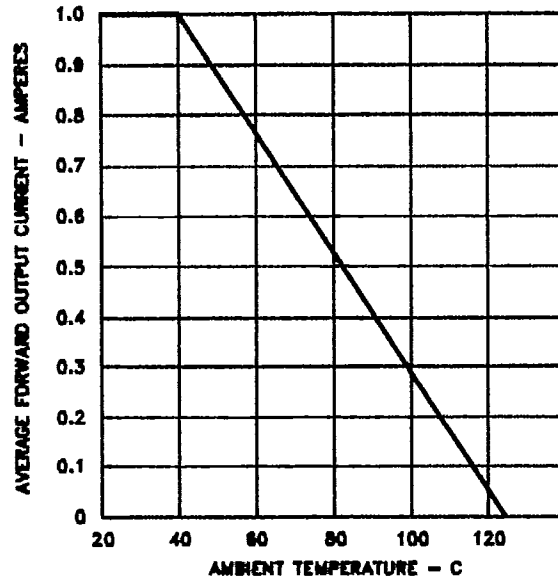


FIG. 3 TYPICAL FORWARD CHARACTERISTICS

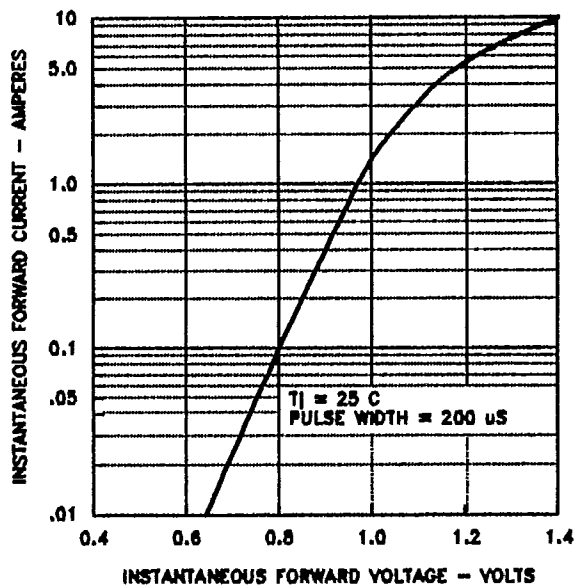
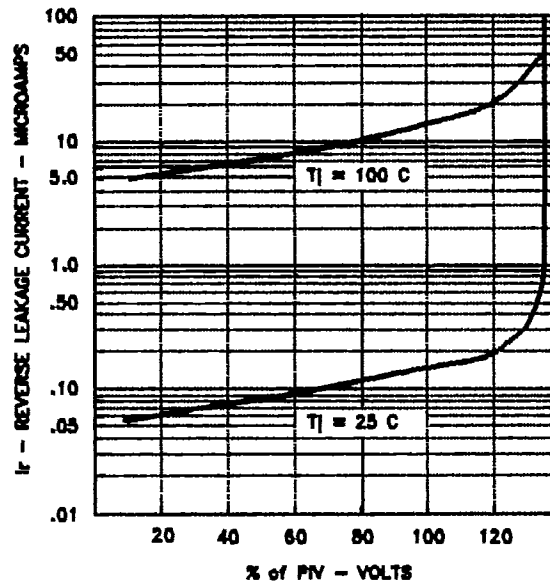


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS



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